

21st RD50 Workshop (CERN)

Thursday, November 15, 2012

Detector Characterization and Simulations (9:00 AM - 3:30 PM)

-Conveners: Eckhart Fretwurst; Vladimir Eremin

time	[id] title	presenter
9:00 AM	[3] Irradiation study on diodes of different silicon materials for the CMS tracker upgrade	ERFLE, Joachim
9:15 AM	[24] Impact of proton irradiations on the electrical properties of n-type Si-diodes	Ms NEUBÜSER, Coralie
9:30 AM	[50] Measurements on 800 MeV proton irradiated diodes (moved from Wednesday!)	JUNKES, Alexandra
9:40 AM	[32] First investigation of silicon microstrips for the CMS tracker upgrade using edge-TCT	FERNANDEZ GARCIA, Marcos
10:00 AM	[8] Temperature dependence of the bulk current in Si	CHILINGAROV, Alexandre
10:20 AM	[15] Charge collection studies on heavily irradiated diodes from the RD50 multiplication run (an update)	KRAMBERGER, Gregor
10:40 AM	Coffee Break	
11:10 AM	[31] Annealing of Heavy Irradiated n-on-p Diodes at Temperatures 20°, 40°, 60° and 80°C	MIKESTIKOVA, Marcela
11:30 AM	[10] TCT measurements with irradiated strip detectors	MANDIC, Igor
11:50 AM	[7] Electrical characterisation of heavily irradiated microstrip sensors	Dr CHILINGAROV, Alexandre
12:10 PM	[0] Simulation of irradiated silicon p-bulk sensors	BOMBEN, Marco
12:30 PM	[21] Simulation of electric field profile in Si irradiated detectors with a consideration of carrier generation parameters	Dr VERBITSKAYA, Elena
12:50 PM	Lunch	
2:00 PM	[30] Simulation of an effective 2-trap radiation damage model	EBER, Robert
2:20 PM	[35] Double Electric field Peak Simulation of Irradiated Detectors Using TCAD tools	BHARDWAJ, Ashutosh
2:40 PM	[45] Simulation of Double Junction using Synopsys TCAD	MOLL, Michael
3:00 PM	[29] Discussion on Detector Characterization and Simulations	FRETWURST, Eckhart EREMIN, Vladimir